

# **SENSITRON**

## **SEMICONDUCTOR**

**1N5822DP**  
**HERMETIC SCHOTTKY BARRIER**  
**RECTIFIER**

TECHNICAL DATA  
 DATA SHEET 5465, REV. B.4

### **3A SCHOTTKY BARRIER RECTIFIER**



- **3A, 40V Schottky Barrier Rectifier**
- **Hermetically sealed power package**
- **Mounts on same footprint as the US package (1N5822US)**
- **MIL-PRF-19500 screening and QCI available (see part ordering information)**

#### **ELECTRICAL CHARACTERISTICS**

<b>RATING</b>	<b>CONDITIONS</b>	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNIT</b>
Working Peak Reverse Voltage ( $V_{RWM}$ )		40	-	-	V
Average Rectified Output Current ( $I_o$ )		-	-	3.0	A
Surge Peak Forward Current ( $I_{FSM}$ ) @ $T_A=25^\circ\text{C}$	$t_p = 8.3$ ms, Half Sine Wave	-	-	80	A
Thermal Resistance ( $R_{\theta JX}$ )		-	-	15	$^\circ\text{C}/\text{W}$
Junction Temperature ( $T_J$ )	-	-65	-	+125	$^\circ\text{C}$
Storage Temp. ( $T_{stg}$ )	-	-65	-	+150	$^\circ\text{C}$

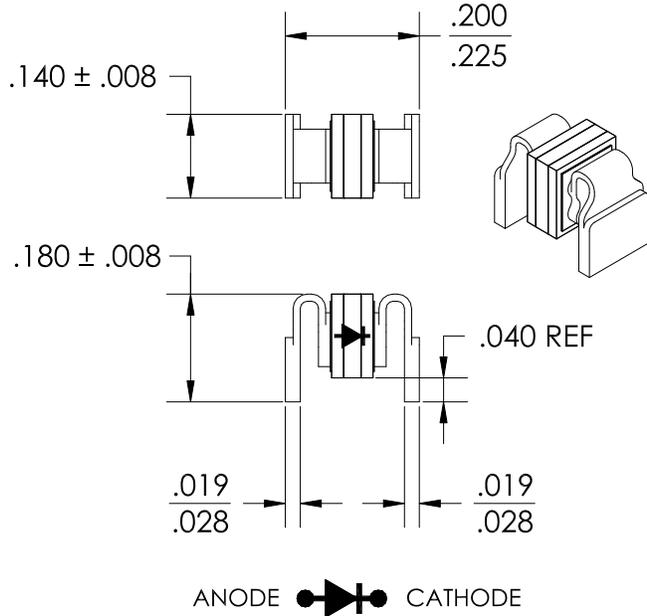
<b>CHARACTERISTIC</b>	<b>CONDITIONS</b>	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNIT</b>
Maximum Forward Voltage ( $V_{f1}$ ) ( $V_{f2}$ ) ( $V_{f3}$ ) ( $V_{f5}$ ) ( $V_{f4}$ )	$I_F = 1.0\text{A}$	-	-	0.40	V
	$I_F = 3.0\text{A}$			0.50	
	$I_F = 9.4\text{A}$			0.70	
	$I_F = 3.0\text{A}, T_A = 100^\circ\text{C}$			0.47	
	$I_F = 3.0\text{A}, T_A = -55^\circ\text{C}$			0.62	
Maximum Reverse Leakage Current $I_{RM}$ @ $V_{RM}$	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$ $T_A = -55^\circ\text{C}$	-	-	0.10 12.5 0.40	mA

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**PACKAGE DIMENSIONS:**



**PART ORDERING INFORMATION:**

**1N5822DP XX X**

Part Number

**Screening Level (blank is no screening):**

Suffix	Screened in Accordance with:
blank	No screening level
SX	MIL-PRF-19500, TX Level
SV	MIL-PRF-19500, TXV Level
SS	MIL-PRF-19500, S Level

**QCI (blank is no QCI):**

Suffix	Inspection
blank	No QCI
Q	MIL-PRF-19500 QCI

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